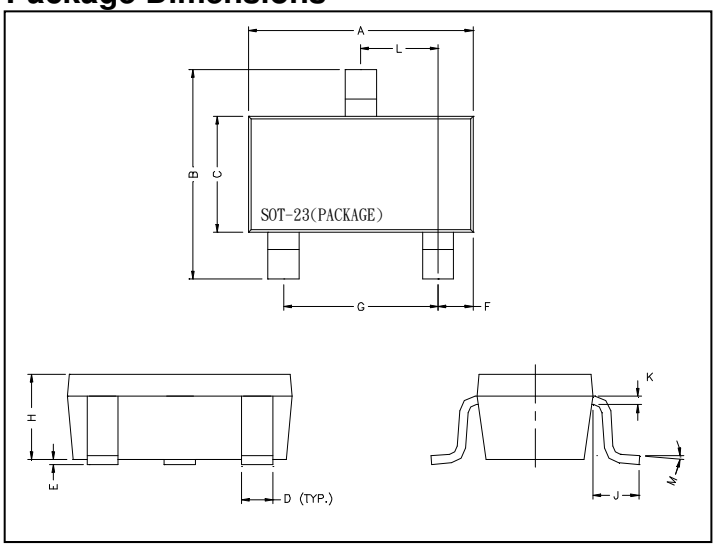
GBAW56

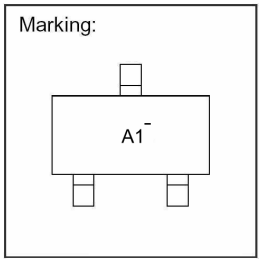
SURFACE MOUNT, SWITCHING DIODE

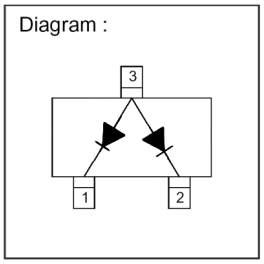
Description

The GBAW56 consists of two high-speed switching diodes with common anodes, fabricated in planar technology, and encapsulated in a small SOT-23 plastic SMD package.

Package Dimensions







Style: Pin 1.Cathode 2.Cathode 3. Common Anode

REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	2.70	3.10	G	1.90	REF.
B	2.40	2.80	H	1.00	1.30
C	1.40	1.60	K	0.10	0.20
D	0.35	0.50	J	0.40	-
E	0	0.10	L	0.85	1.15
F	0.45	0.55	M	0°	10°

Absolute Maximum Ratings at T_A = 25℃

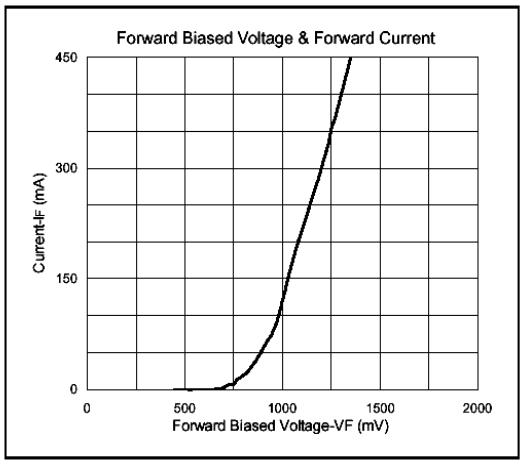
Parameter		Symbol	Ratings	Unit
Junction Temperature		Tj	+125	℃
Storage Temperature		Tstg	-65 ~ +150	℃
Repetitive Peak Reverse Voltage		V_{RRM}	85	V
Continuous Reverse Voltage		V_R	75	V
Continuous Forward Current	single diode loaded (note1)	I_F	150	mA
	double diode loaded (note1)		130	
Repetitive Peak Forward Current		I_{FRM}	500	mA
Non-Repetitive Peak Forward Current (1ms)		I_{FSM}	1	A
Total Power Dissipation		P_D	250	mW

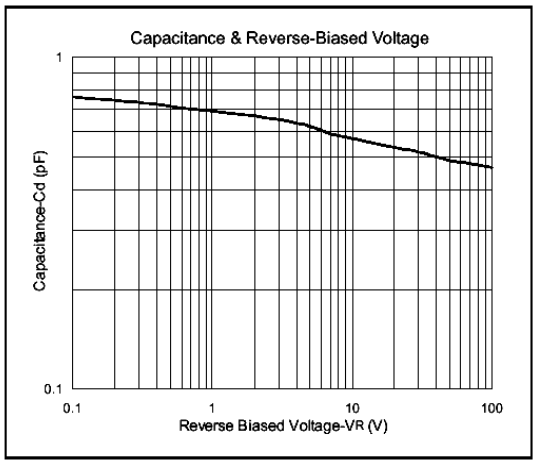
Notes: 1. Device mounted on an FR4 printed-circuit board.

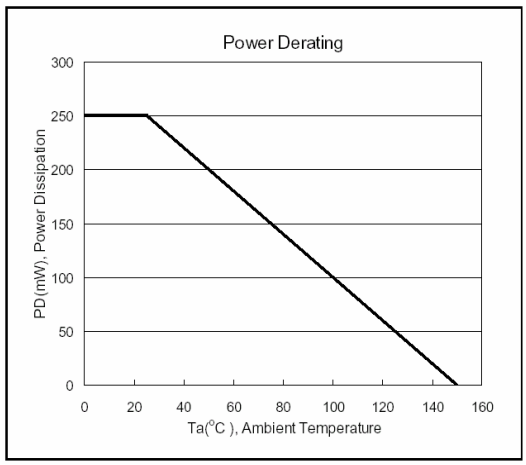
Electrical Characteristics (at T_A = 25℃ unless otherwise noted)

Parameter	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Voltage	V_R	85	-	V	I_R=100uA
Forward Voltage	V_F(1)	-	715	mV	I_F=1mA
	V_F(2)	-	855	mV	I_F=10mA
	V_F(3)	-	1000	mV	I_F=50mA
	V_F(4)	-	1250	mV	I_F=150mA
Reverse Current	I_R	-	1	uA	V_R=80V
Diode Capacitance	C_D		2	pF	V_R=0, f=1MHz
Reverse Recovery Time	Trr	-	4	nS	I_F=I_R=10mA, R_L=100Ω measured at I_R=1mA

Characteristics Curve







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